

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M22-2113		PRIORITY SERIAL NO. 1041,134	
LIST OF ART CITED BY APPLICANT <small>(Use several sheets if necessary)</small>				APPLICANT Cem Basceri et al.			
				PRIORITY FILING DATE May 21, 2003		PRIORITY GROUP 319	
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
MA	AA	5,292,673	03-1994	Shinraki et al.	—	—	—
MA	AB	5,486,488	01-1996	Kamijima	—	—	—
MA	AC	5,641,702	06-1997	Imai et al.	—	—	—
MA	AD	5,726,083	03-1998	Takashi	—	—	—
MA	AE	5,893,734	04-1999	Jeng et al.	—	—	—
MA	AF	6,117,725	09-2000	Huang	—	—	—
MA	AG	6,200,893	03-2001	Sneh	—	—	—
MA	AH	6,235,572	05-2001	Kumitono et al.	—	—	—
MA	AI	6,399,438	06-2002	Saito et al.	—	—	—
MA	AJ	6,511,896	1/28/03	Basceri et al.	—	—	—
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AK						
	AL						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
MA	AM		Bia Yu, et al., "70nm MOSFET with Ultra-Shallow, Abrupt, and Super-Doped S/D Extension Implemented by Laser Thermal Process (LTP)", IEEE, 03/1999.				
MA	AM		Somit Talwar, et al., "Ultra-Shallow, Abrupt, and Highly-Activated Junctions by Low-Energy Ion Implantation and Laser Annealing", Verdant Technologies, San Jose, CA.				
MA	AO		Ken-ichi Ooto, et al., "Ultra-Low Contact Resistance for Deca-nm MOSFETs by Laser Annealing", IEEE, 09/1999, pps. 20.7.1-20.7.3.				
EXAMINER				DATE CONSIDERED			
Renee K. Day				11-1-04			
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							

EW 37 245 4 1:0